

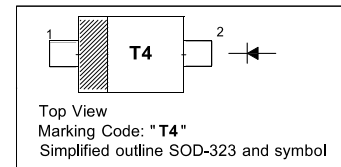
BAS16WS Silicon Epitaxial Planar Switching Diode

Features

- Fast switching diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Forward Current (Continuous)	I_F	250	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1 2	A
		at $t = 1\text{ s}$	
		at $t = 1\text{ ms}$	
		at $t = 1\text{ }\mu\text{s}$	
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage	V_F	0.715	V
at $I_F = 1\text{ mA}$		0.855	
at $I_F = 10\text{ mA}$		1	
at $I_F = 50\text{ mA}$		1.25	
Reverse Leakage Current	I_R	1	μA
at $V_R = 75\text{ V}$		30	
at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$		50	
Diode Capacitance	C_{tot}	2	pF
at $V_R = 0\text{ V}, f = 1\text{ MHz}$			
Reverse Recovery Time	t_{rr}	6	ns
at $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$			

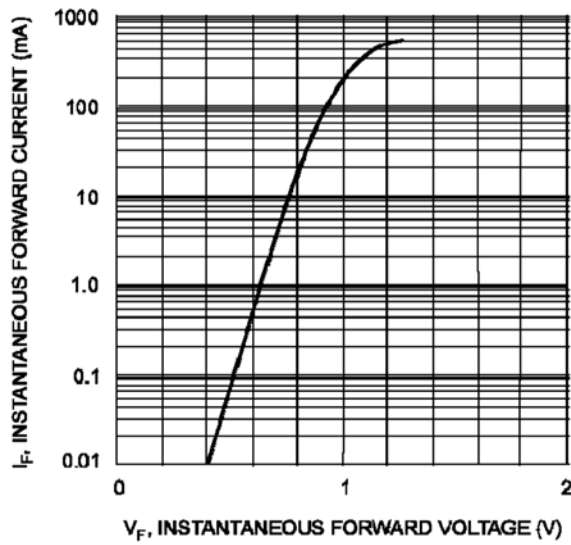


Fig. 1 Forward Characteristics

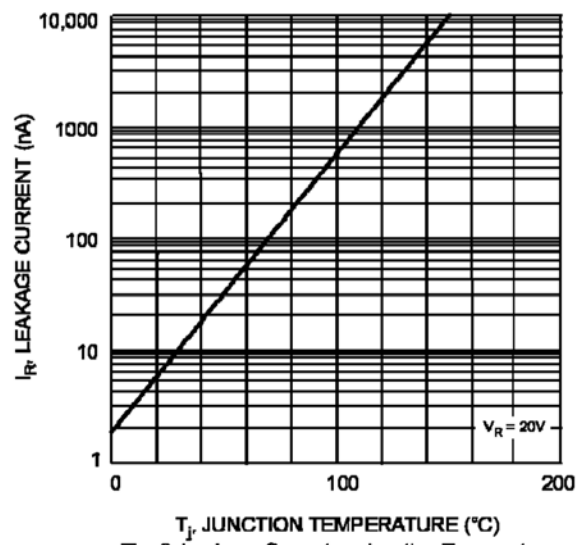


Fig. 2 Leakage Current vs Junction Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

